Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1 (currently amended) A light emitting GaN based device, comprising:

a semiconductor device that emits light having a wavelength in the range of 200 nm to 620 nm; and

a red phosphor comprising a vanadate combined with yttrium, gadolinium and/or lanthanum and activated with trivalent having the formula:

$$Bi_xLn_{1-x}VO_4:A$$

where x is greater than 0 and less than 1, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu³⁺, Sm³⁺ and Pr³⁺, or any combination thereof, with or without Tb³⁺ as a co-dopant.

2 (original) The device of claim 1 in which the red phosphor absorbs light of a wavelength in the range of 240 nm to 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm.

3 (original) The device of claim 1 containing at least one non- red phosphor in addition to said red phosphor.

4 (original) The device of claim 1 containing a green phosphor and a blue phosphor in addition to said red phosphor.

5 (currently amended) The device of claim [[1]] 30 in which said red phosphor has the formula:

where x = 0 to 1, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu³⁺, Sm³⁺ and Pr³⁺, or any combination thereof, with or without Tb³⁺ as a co-dopant.

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6 (original) The device of claim 5 in which x is greater than 0 and less than 1.

7 (original) The device of claim 6 in which x is 0.05 to 0.5.

8 (original) The device of claim 5 including Tb³⁺ as a co-dopant.

9 (currently amended) The device of claim [[1]] <u>29</u> in which the semiconductor device is a GaN based device.

10 (original) The device of claim 1 in which the semiconductor device is a vertical cavity surface emitting laser, a light emitting diode, or a laser diode.

11 (currently amended) The device of claim [10] <u>29</u> in which the semiconductor device is a GaN based device.

12 (original) The device of claim 11 in which the semiconductor device is a light emitting diode.

13 (currently amended) The device of claim [[5]] 1 containing a green phosphor and a blue phosphor in addition to said red phosphor and in which said green phosphor is ZnS:Cu⁺,Al³⁺) ZnS:(Cu⁺,Al³⁺) and said red blue phosphor is BaMgAl₁₀O₁₇:Eu²⁺.

14 (original) A light emitting semiconductor device, comprising:

a GaN based light emitting diode that emits light having a wavelength in the range of 200 nm to 620 nm;

a red phosphor that absorbs light of a wavelength in the range of 240 nm to 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm, having the formula:

$$Bi_xLn_{1-x}VO_4:A$$

where x is 0.05 to 0.5, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu^{3+} , Sm^{3+} and Pr^{3+} , or any combination thereof, with or without Tb^{3+} as a co-dopant;

a green phosphor; and

a blue phosphor.

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- 15 (original) The device of claim 14 including Tb³⁺ as a co-dopant.
- 16 (currently amended) The device of claim 14 in which said green phosphor is ZnS:Cu⁺,Al³⁺) ZnS:(Cu⁺,Al³⁺) and said blue phosphor is BaMgAl₁₀O₁₇:Eu²⁺.
- 17 (currently amended) A white light emitting phosphor combination, comprising:
 a red phosphor comprising a vanadate combined with yttrium, gadolinium and/or
 lanthanum and activated with trivalent having the formula:

$$\underline{\text{Bi}_{x}\text{Ln}_{1-x}\text{VO}_{4}:A}$$

where x is greater than 0 and less than 1, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from-Eu³⁺, Sm³⁺ and or Pr³⁺, or any combination thereof, with or without Tb³⁺ as a co-dopant;

- a green phosphor; and
- a blue phosphor.
- 18 (original) The phosphor combination of claim 17 in which said red phosphor absorbs light of a wavelength in the range of 240 nm to 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm.
- 19 (currently amended) The phosphor combination of claim [[17]] <u>31</u> in which said red phosphor has the formula:

where x = 0 to 1, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu^{3+} , Sm^{3+} and Pr^{3+} , or any combination thereof, with or without Tb^{3+} as a co-dopant.

- 20 (original) The phosphor combination of claim 19 in which x is greater than 0 and less than 1.
 - 21 (original) The phosphor combination of claim 20 in which x is 0.05 to 0.5.
- 22 (original) The phosphor combination of claim 19 in which said red phosphor includes Tb³⁺ as a co-dopant.

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- 23 (currently amended) The phosphor combination of claim [[19]] <u>17</u> in which said green phosphor is ZnS:Cu⁺,Al³⁺) ZnS:(Cu⁺,Al³⁺) and said blue phosphor is BaMgAl₁₀O₁₇:Eu²⁺ suitable for use in a GaN based device.
- 24 (currently amended) A white light emitting phosphor combination,
 a red phosphor that absorbs said light of a wavelength in the range of 240 nm to
 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm, having the
 formula:

where x is 0.05 to 0.5, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu^{3+} , Sm^{3+} and Pr^{3+} , or any combination thereof, with or without Tb^{3+} as a co-dopant.;

a green phosphor comprising ZnS:Cu⁺,Al³⁺) ZnS:(Cu⁺,Al³⁺); and a blue phosphor comprising BaMgAl₁₀O₁₇:Eu²⁺.

25 (original) The phosphor combination of claim 24 in which said red phosphor includes Tb³⁺ as a co-dopant.

26 (currently amended) A red phosphor that absorbs said light of a wavelength in the range of 240 nm to 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm, having the formula:

$$Bi_xLn_{1-x}VO_4:A$$

where x is greater than 0 and less than 1 0.05 to 0.5, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu³⁺, Sm³⁺ and Pr³⁺, or any combination thereof, with or without Tb³⁺ as a co-dopant.

27 (currently amended The phosphor [[26]] $\underline{32}$ in which x is 0.05 to 0.5.

28 (original) The phosphor 26 in which in which said red phosphor includes Tb³⁺ as a co-dopant.

29 (new) A light emitting device, comprising:

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a semiconductor device that emits light having a wavelength in the range of 200 nm to 620 nm; and

a red phosphor having the formula:

$$Bi_xLn_{1-x}VO_4:A$$

where x is 0.05 to 0.5, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu^{3+} , Sm^{3+} and Pr^{3+} , or any combination thereof, with or without Tb^{3+} as a co-dopant.

- 30 (new) A light emitting device, comprising:
- a semiconductor device that emits light having a wavelength in the range of 200 nm to 620 nm; and
- a red phosphor comprising a vanadate combined with yttrium, gadolinium and/or lanthanum and activated with trivalent Eu³⁺, Sm³⁺ or Pr³⁺, or any combination thereof, with Tb³⁺. as a co-dopant.
 - 31 (new) A white light emitting phosphor combination, comprising:
 - a red phosphor comprising a vanadate combined with yttrium, gadolinium and/or lanthanum and activated with trivalent Eu³⁺, Sm³⁺ and Pr³⁺, or any combination thereof, with Tb³⁺ as a co-dopant;
 - a green phosphor; and
 - a blue phosphor.
 - 32 (new) A red phosphor that absorbs said light of a wavelength in the range of 240 nm to 550 nm and emits red light at a wavelength in the range of 580 nm to 700 nm, having the formula:

where x is greater than 0 and less than 1, Ln is an element selected from the group consisting of Y, La and Gd, and A is an activator selected from Eu³⁺, Sm³⁺ and Pr³⁺, or any combination thereof, with Tb³⁺ as a co-dopant.